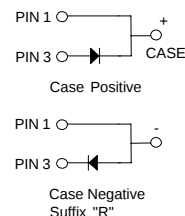


FES16AT - FES16JT



TO-220AC



Features

- Low forward voltage drop.
- High surge current capacity.
- High current capability.
- High reliability.

Fast Rectifiers (Glass Passivated)

Absolute Maximum Ratings*

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value								Units
		16AT	16BT	16CT	16DT	16FT	16GT	16HT	16JT	
V_{RRM}	Maximum Repetitive Reverse Voltage	50	100	150	200	300	400	500	600	V
$I_{F(AV)}$	Average Rectified Forward Current, .375" lead length @ $T_A = 100^\circ\text{C}$	16								A
I_{FSM}	Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-Wave	250								A
T_{stg}	Storage Temperature Range	-65 to +150								°C
T_J	Operating Junction Temperature	-65 to +150								°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics

Symbol	Parameter	Value	Units
P_D	Power Dissipation	7.81	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	16	°C/W
$R_{\theta JL}$	Thermal Resistance, Junction to Lead	1.2	°C/W

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Device								Units
		16AT	16BT	16CT	16DT	16FT	16GT	16HT	16JT	
V _F	Forward Voltage @ 8.0A	0.95				1.3		1.5		V
t _{rr}	Reverse Recovery Time I _F = 0.5 A, I _R = 1.0 A, I _{RR} = 0.25 A	35				50				ns
I _R	Reverse Current @ rated V _R T _A = 25°C T _A = 100°C	10 500								μA μA
C _T	Total Capacitance V _R = 4.0. f = 1.0 MHz	170						145		pF

Typical Characteristics

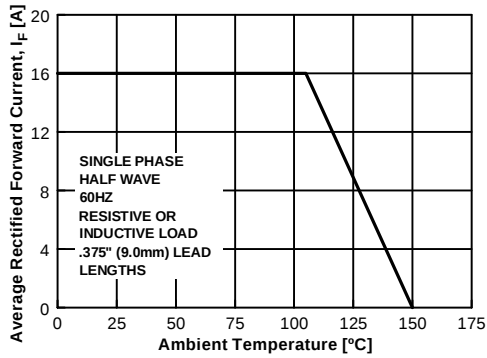


Figure 1. Forward Current Derating Curve

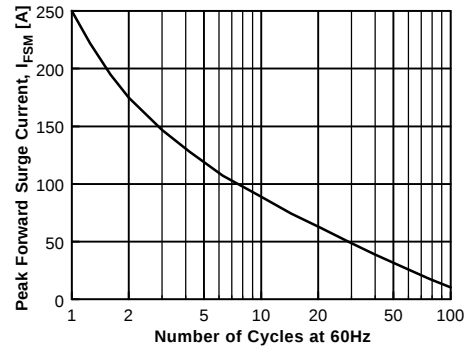


Figure 2. Non-Repetitive Surge Current

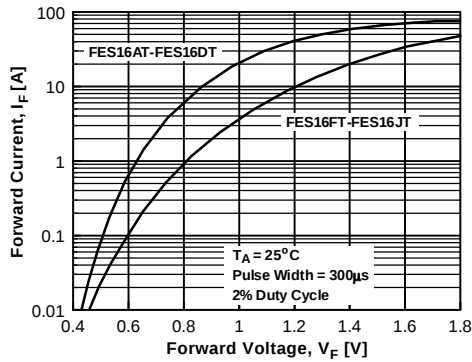


Figure 3. Forward Voltage Characteristics

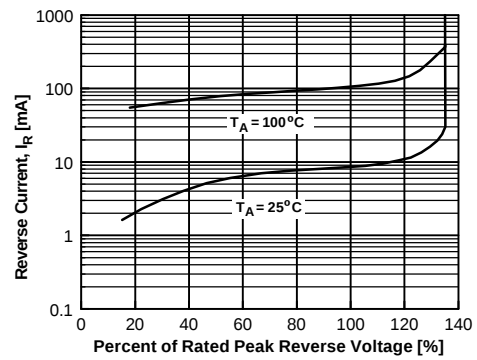


Figure 4. Reverse Current vs Reverse Voltage

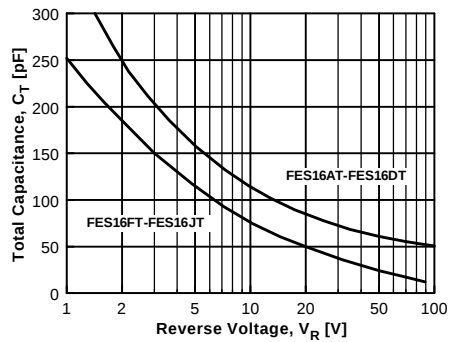
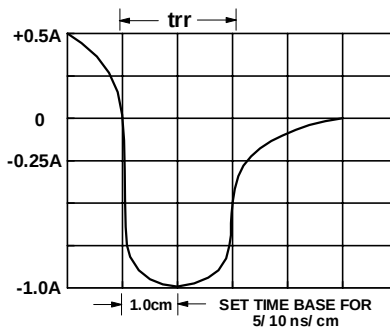
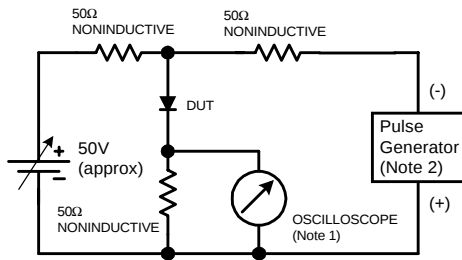


Figure 5. Total Capacitance



Reverse Recovery Time Characteristic and Test Circuit Diagram

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE ^{Ex} ™	FAST [®]	OPTOLOGIC™	SMART START™	VCX™
Bottomless™	FAST ^r ™	OPTOPLANAR™	STAR*POWER™	
CoolFET™	FRFET™	PACMAN™	Stealth™	
CROSSVOLT™	GlobalOptoisolator™	POP™	SuperSOT™-3	
DenseTrench™	GTO™	Power247™	SuperSOT™-6	
DOME™	HiSeC™	PowerTrench [®]	SuperSOT™-8	
EcoSPARK™	ISOPLANAR™	QFET™	SyncFET™	
E ² CMOS™	LittleFET™	QS™	TinyLogic™	
EnSigna™	MicroFET™	QT Optoelectronics™	TruTranslation™	
FACT™	MicroPak™	Quiet Series™	UHC™	
FACT Quiet Series™	MICROWIRE™	SILENT SWITCHER [®]	UltraFET [®]	

STAR*POWER is used under license

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.



**Стандарт
Электрон
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331